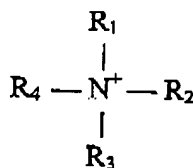


In the Claims:

1. (Original) An aqueous polishing composition comprising:
 a corrosion inhibitor for limiting removal of an interconnect metal;
 an acidic pH;
abrasive particles; and
 an organic-containing ammonium salt formed with



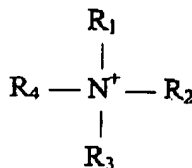
R_1 , R_2 , R_3 and R_4 are radicals, R_1 is an unsubstituted aryl, alkyl, aralkyl, or alkaryl group that has a carbon chain length of 2 to 15 carbon atoms and the organic-containing ammonium salt has a concentration that accelerates TEOS removal and decreases removal of at least one coating selected from the group consisting of SiC, SiCN, Si₃N₄ and SiCO with at least one polishing pressure less than 21.7 kPa.

2. (Currently Amended) The composition of Claim 1, wherein R_1 is a ~~substituted or unsubstituted aryl, alkyl, aralkyl, or alkaryl group that comprises~~ has 2 to 5 carbon atoms.

3. (Currently amended) The composition of Claim 1, wherein the ammonium salt is formed with a compound ~~comprising~~ selected from tetraethyl ammonium, tetrabutylammonium, benzyltributylammonium, benzyltrimethylammonium, benzyltriethylammonium, diallyldimethylammonium, diethylaminoethyl methacrylate, dimethylaminoethyl methacrylate, methacryloyloxyethyltrimethylammonium, 3-(methacrylamido) propyltrimethylammonium, triethylenetetramine, tetramethylguanidine, hexylamine and mixtures thereof.

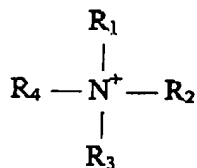
4. (Original) An aqueous polishing composition comprising, by weight percent:
 0.05 to 15 abrasive particles;
 0 to 10 oxidizing agent;

0.0025 to 6 a corrosion inhibitor for limiting removal of an interconnect metal;
 a pH of less than 5; and
 0.001 to 3 organic-containing ammonium salt formed with



R_1 , R_2 , R_3 and R_4 are radicals, R_1 is an unsubstituted aryl, alkyl, aralkyl, or alkaryl group that has a carbon chain length of 2 to 15 carbon atoms and the organic-containing ammonium salt has a concentration that accelerates TEOS removal and decreases removal of at least one coating selected from the group consisting of SiC, SiCN, Si₃N₄ and SiCO with at least one polishing pressure less than 21.7 kPa.

5. (Original) The composition of Claim 4, wherein the abrasive comprises a silica, the oxidizing agent comprises hydrogen peroxide, the corrosion inhibitor comprises benzotriazole and the composition has a pH of less than 3 and an organic fluoride ammonium salt.
6. (Original) The composition of Claim 5, wherein the polishing composition has a pH of 2 to 3 adjusted with nitric acid.
7. (Original) The composition of Claim 4, wherein R_1 has a carbon chain length of 2 to 5.
8. (Cancelled) A method for removing a layer from a semiconductor substrate comprising:
 applying an aqueous polishing composition to the semiconductor substrate, the aqueous polishing composition comprising an organic-containing ammonium salt formed with



R_1 , R_2 , R_3 and R_4 are radicals, R_1 has a carbon chain length of 2 to 15 carbon atoms to accelerate removal of a silicon oxide-containing layer; and

polishing layer the silicon oxide-containing layer from the semiconductor substrate with a polishing pad to remove the silicon oxide-containing layer.

9. (Cancelled) The method of claim 1 including the additional step of polishing a barrier layer with the aqueous polishing composition before removing the silicon oxide-containing layer.
10. (Cancelled) The method of claim 1 wherein the TEOS layer is a top layer deposited on a bottom layer, the bottom layer comprises a coating selected from the group consisting of SiC , SiCN , Si_3N_4 and SiCO and the removing removes the top layer and leaves at least a portion of the bottom layer.
11. (New) An aqueous polishing composition comprising, by weight percent:
 - 0.1 to 10 silica particles;
 - 0 to 10 oxidizing agent;
 - 0.25 to 4 benzotriazole;
 - a pH of 1.5 to 4 adjusted with an inorganic adjusting agent; and
 - 0.02 to 2 organic-containing ammonium salt selected from at least one of tetraethyl ammonium salts, tetrabutylammonium salts, benzyltributylammonium salts, benzyltrimethylammonium salts and benzyltriethylammonium salts.
12. (New) The composition of Claim 11, wherein the organic-containing inorganic salt is a tetrabutylammonium salt.
13. (New) The composition of Claim 11, wherein the polishing composition has a pH of 2 to 3 adjusted with nitric acid.